ELECTRONICS, INC.
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NTE2647 (PNP) & NTE2648 (NPN)
Silicon Complementary Transistors
General Purpose Amp

Features:

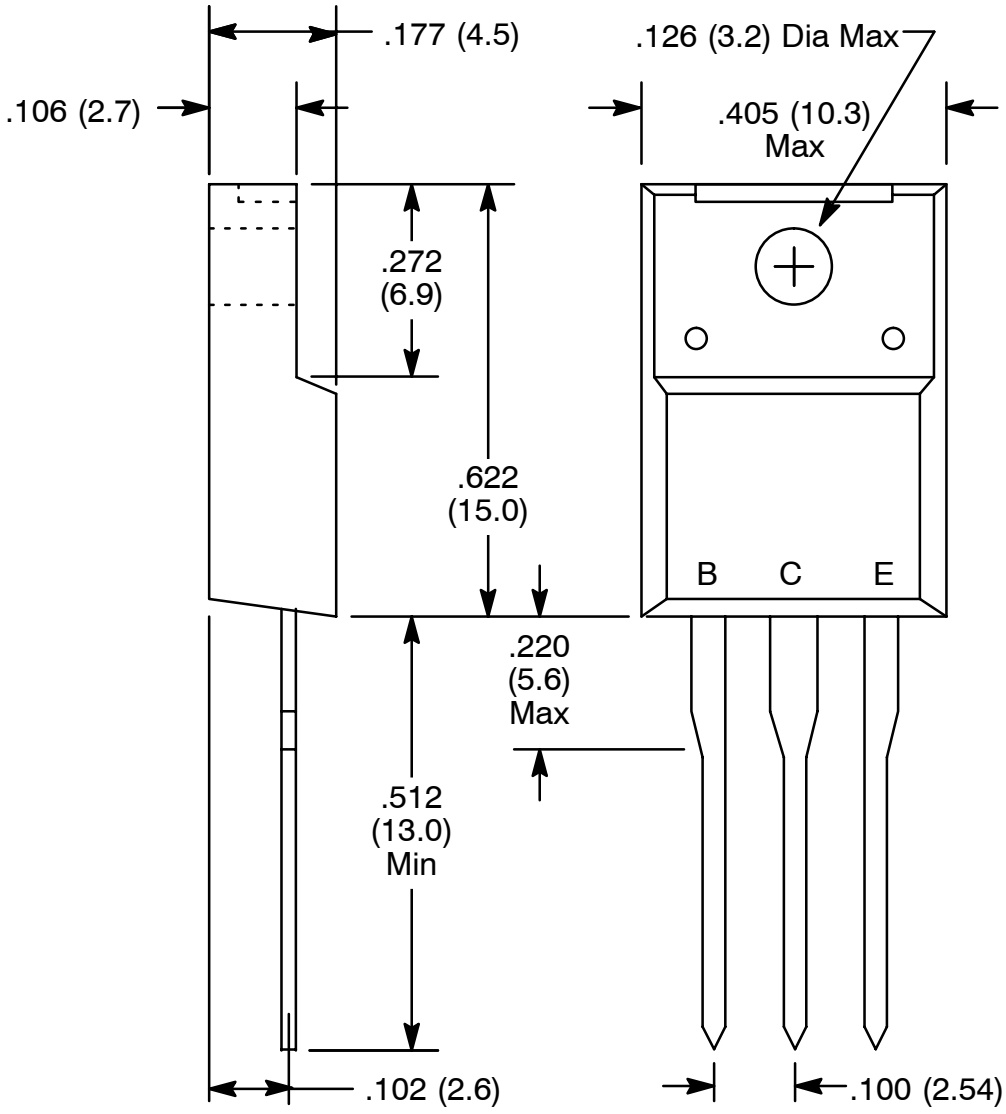
- High Transition Frequency

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 230V
Collector–Emitter Voltage, V_{CEO} 230V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C 1A
Collector Power Dissipation, P_C
T_A = +25°C 2.0W
T_C = +25°C 20W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 230V, I_E = 0	–	–	1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = V, I_C = 0	–	–	1.0	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	230	–	–	V
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 100mA	100	–	320	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	–	–	1.5	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 500mA	–	–	1.0	V
Transition Frequency NTE2747	f_T	V_{CE} = 10V, I_C = 100mA	–	70	–	MHz
NTE2748			–	100	–	MHz
Collector Output Capacitance NTE2647	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	30	–	pF
NTE2748			–	20	–	pF


.177 (4.5)
.106 (2.7)
.126 (3.2) Dia Max
.405 (10.3)
Max
.272
(6.9)
.622
(15.0)
B
C
E
.220
(5.6)
Max
.512
(13.0)
Min
.102 (2.6)
.100 (2.54)